

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1-13. (Cancelled)

14. (Original) A method for performing a multi-step etch within a semiconductor-based device processing apparatus, the semiconductor-based device processing apparatus including a barrier having a first position relative to a wafer facilitative of a first etch process and having a second position relative to the wafer facilitative of a second etch process, the method comprising:

performing a first etch process with the barrier in the first position relative to the wafer;

changing the position of the barrier relative to the wafer from the first position relative to the wafer to the second position relative to the wafer; and

performing a second etch process with the barrier in the second position relative to the wafer.

15. (Original) A method as recited in claim 14 wherein changing the position of the barrier relative to the wafer is performed by moving the barrier.

16. (Original) A method as recited in claim 14 wherein the first etch process is a chemically driven etch.

17. (Original) A method as recited in claim 16 wherein the first etch process is a metal etch.

18. (Original) A method as recited in claim 16 wherein the second etch process is an ion assisted etch.

19. (Original) A method as recited in claim 14 wherein the first etch process is an ion assisted etch.

20. (Original) A method as recited in claim 19 wherein the second etch process is a chemically driven etch.

21. (Original) A method as recited in claim 14 further including a third etch.

22. (Original) A method as recited in claim 21 wherein the third etch occurs between the first and the second etch.